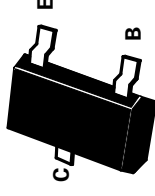


# SOT23 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 2 – SEPTEMBER 95

# BSS63



COMPLIMENTARY TYPE — BSS64

PARTMARKING DETAIL — BSS63 - T3  
BSS63R - T6

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-110	V
Collector-Emitter Voltage	$V_{CEO}$	-100	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Continuous Collector Current	$I_C$	-100	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{TOT}$	330	mW
Operating and Storage Temperature Range	$t_j, t_{stg}$	-55 to +150	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ ).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)}$	-110		V	$I_C = -10\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-100		V	$I_C = -100\mu A^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6		V	$I_E = -10\mu A$
Collector Cut-Off Current	$I_{EBO}$		-100 -50	nA $\mu A$	$V_{CB} = -90V, V_{CE} = -90V, T_{amb} = 150^{\circ}C$
Emitter Cut-Off Current	$I_{EBO}$		-200	nA	$V_{EB} = -6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-250	mV	$I_C = -25mA, I_B = -2.5mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-900	mV	$I_C = -25mA, I_B = -2.5mA$
Static Forward Current	$h_{FE}$	30 30			$I_C = -10mA, V_{CE} = -1V, I_C = -25mA, V_{CE} = 1V$
Transition Frequency	$f_T$	50	Typ. 85	MHz	$V_{CE} = -5V, I_C = -25mA, f = 35 MHz$
Output Capacitance	$C_{obo}$		Typ. 3	pF	$V_{CB} = -10V, f = 1MHz$

\* Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$